PROCESS CP591

Small Signal Transistor

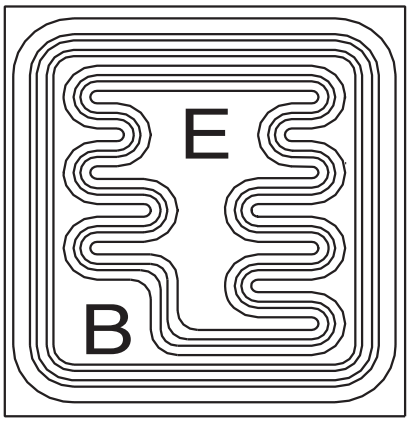
PNP - Amp/Switch Transistor Chip

Central™ Semiconductor Corp.

PROCESS DETAILS

Process	EPITAXIAL PLANAR
Die Size	19 x 19 MILS
Die Thickness	9.0 MILS
Base Bonding Pad Area	3.5 x 4.3 MILS
Emitter Bonding Pad Area	3.5 x 4.5 MILS
Top Side Metalization	Al - 30,000Å
Back Side Metalization	Au - 18,000Å

GEOMETRY



BACKSIDE COLLECTOR R0

GROSS DIE PER 4 INCH WAFER

30,600

PRINCIPAL DEVICE TYPES

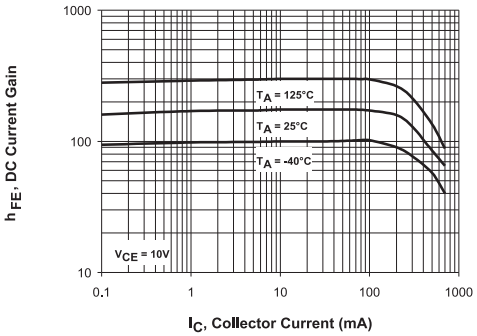
2N2905A
2N2907A
CMPT2907A
CMST2907A
CXT2907A
CZT2907A
PN2907A

145 Adams Avenue
Hauppauge, NY 11788 USA
Tel: (631) 435-1110
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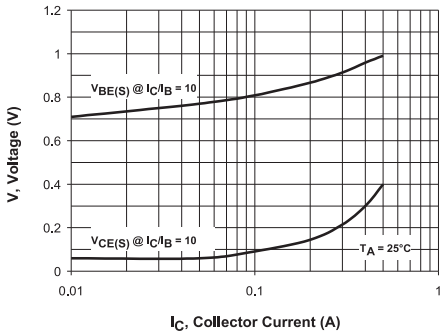
R3 (1-August 2002)

Typical Electrical Characteristics

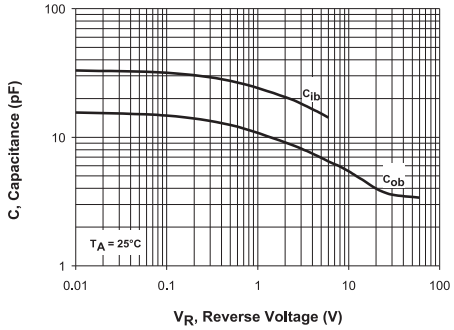
DC Current Gain



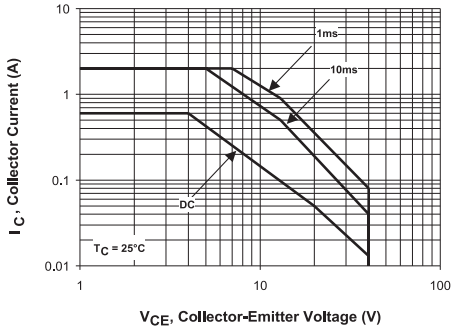
"ON" Voltage



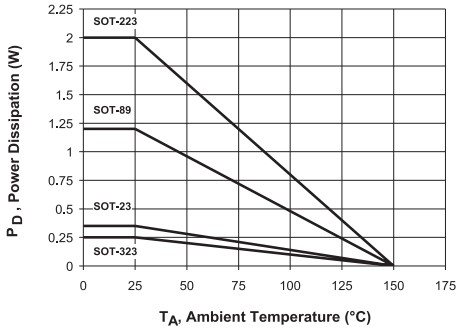
Capacitance



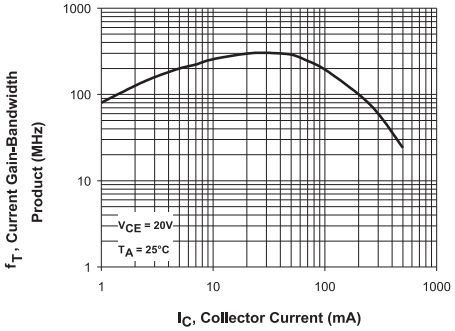
Safe Operating Area



Power Derating



Current Gain-Bandwidth Product



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